

# BAV99WT1, BAV99RWT1

Preferred Devices

## Dual Series Switching Diodes

The BAV99WT1 is a smaller package, equivalent to the BAV99LT1.

### Features

- Pb-Free Packages are Available

### Suggested Applications

- ESD Protection
- Polarity Reversal Protection
- Data Line Protection
- Inductive Load Protection
- Steering Logic

### MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltage	$V_R$	70	Vdc
Forward Current	$I_F$	215	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Repetitive Peak Reverse Voltage	$V_{RRM}$	70	V
Average Rectified Forward Current (Note 1) (averaged over any 20 ms period)	$I_{F(AV)}$	715	mA
Repetitive Peak Forward Current	$I_{FRM}$	450	mA
Non-Repetitive Peak Forward Current $t = 1.0 \mu s$ $t = 1.0 ms$ $t = 1.0 S$	$I_{FSM}$	2.0 1.0 0.5	A

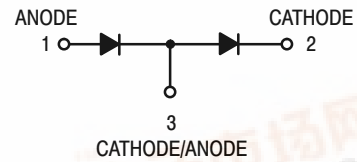
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

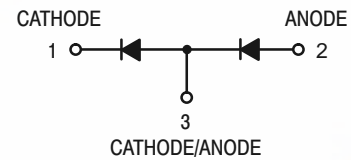


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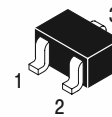


BAV99WT1  
SC-70  
CASE 419, STYLE 9

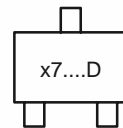


BAV99RWT1  
SC-70  
CASE 419, STYLE 10

### MARKING DIAGRAM



SC-70  
CASE 419



A7 = BAV99WT1  
F7 = BAV99RWT1  
D = Date Code

### ORDERING INFORMATION

Device	Package	Shipping†
BAV99WT1	SC-70	3000/Tape & Reel
BAV99WT1G	SC-70 (Pb-Free)	3000/Tape & Reel
BAV99RWT1	SC-70	3000/Tape & Reel
BAV99RWT1G	SC-70 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.



# BAV99WT1, BAV99RWT1

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	200 1.6	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

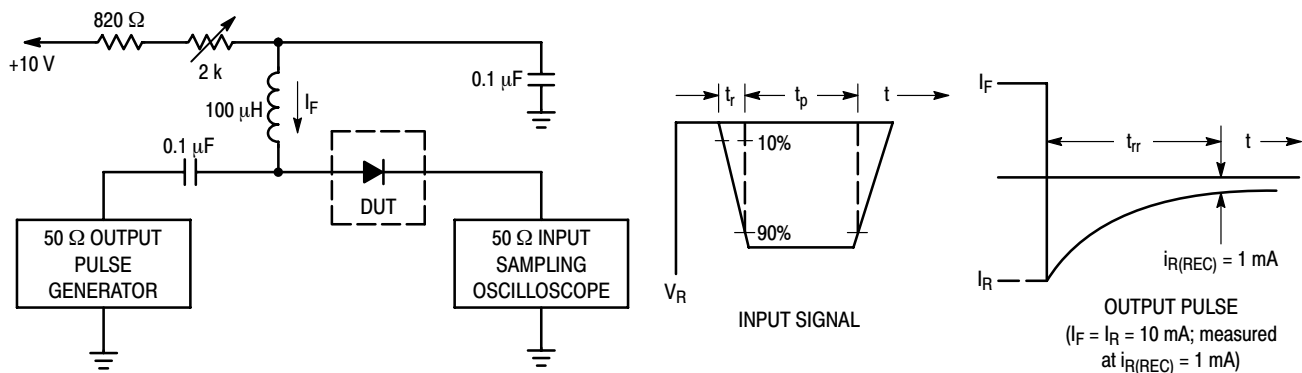
## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
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## OFF CHARACTERISTICS

Reverse Breakdown Voltage ( $I_{BR} = 100 \mu\text{A}$ )	$V_{(BR)}$	70	-	Vdc
Reverse Voltage Leakage Current ( $V_R = 70 \text{ Vdc}$ ) ( $V_R = 25 \text{ Vdc}, T_J = 150^\circ\text{C}$ ) ( $V_R = 70 \text{ Vdc}, T_J = 150^\circ\text{C}$ )	$I_R$	- - -	2.5 30 50	$\mu\text{Adc}$
Diode Capacitance ( $V_R = 0, f = 1.0 \text{ MHz}$ )	$C_D$	-	1.5	pF
Forward Voltage ( $I_F = 1.0 \text{ mAdc}$ ) ( $I_F = 10 \text{ mAdc}$ ) ( $I_F = 50 \text{ mAdc}$ ) ( $I_F = 150 \text{ mAdc}$ )	$V_F$	- - - -	715 855 1000 1250	mVdc
Reverse Recovery Time ( $I_F = I_R = 10 \text{ mAdc}$ , $i_{R(REC)} = 1.0 \text{ mAdc}$ ) (Figure 1) $R_L = 100 \Omega$	$t_{rr}$	-	6.0	ns
Forward Recovery Voltage ( $I_F = 10 \text{ mA}$ , $t_f = 20 \text{ ns}$ )	$V_{FR}$	-	1.75	V

- FR-5 =  $1.0 \times 0.75 \times 0.062 \text{ in.}$
- Alumina =  $0.4 \times 0.3 \times 0.024 \text{ in.}$  99.5% alumina.



- Notes: (a) A 2.0 k $\Omega$  variable resistor adjusted for a Forward Current ( $I_F$ ) of 10 mA.  
 (b) Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to 10 mA.  
 (c)  $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

# BAV99WT1, BAV99RWT1

## CURVES APPLICABLE TO EACH DIODE

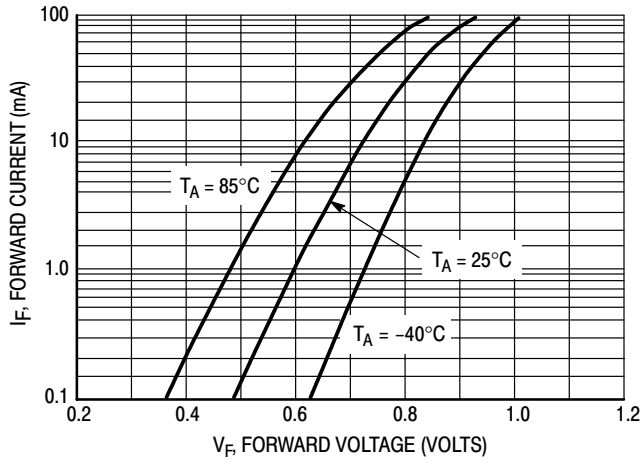


Figure 2. Forward Voltage

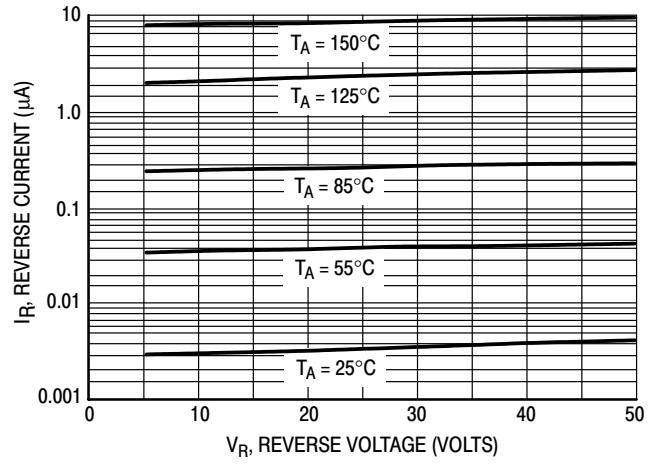


Figure 3. Leakage Current

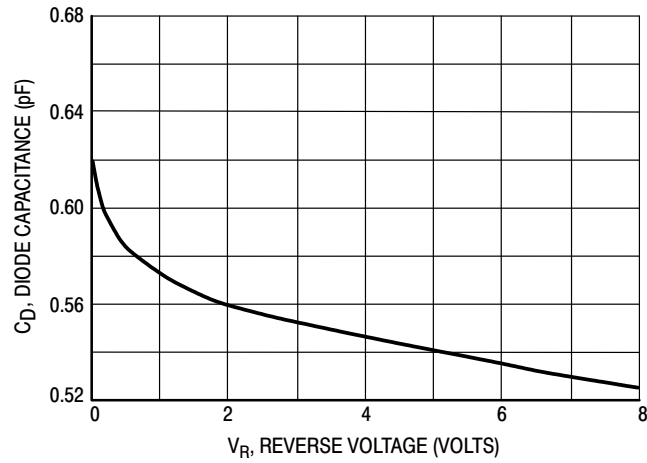
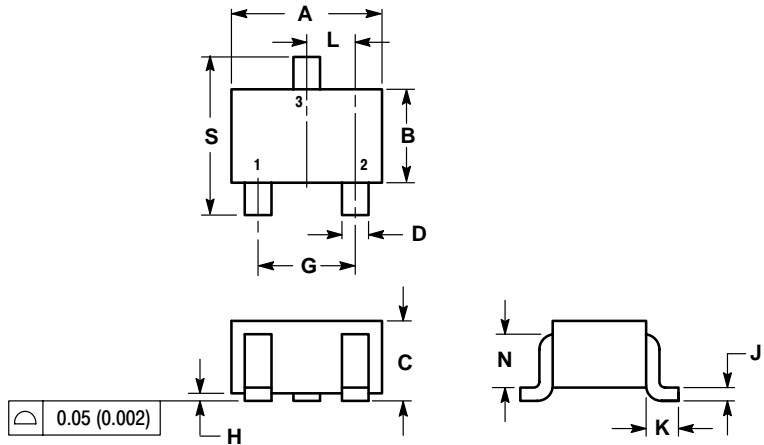


Figure 4. Capacitance

# BAV99WT1, BAV99RWT1

## PACKAGE DIMENSIONS

SC-70 (SOT-323)  
CASE 419-04  
ISSUE L



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
S	0.079	0.095	2.00	2.40

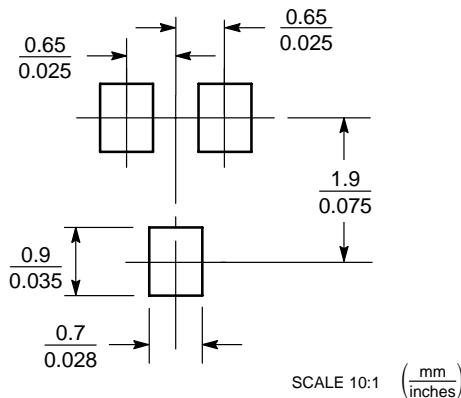
**STYLE 9:**

- PIN 1. ANODE
- CATHODE
- CATHODE-ANODE


**STYLE 10:**

- PIN 1. CATHODE
- ANODE
- ANODE-CATHODE

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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